

## 25V N-Channel MOSFET



SOP-8

#### Pin Definition:

- 1. Source
- 2. Source
- 3. Source
- 4. Gate
- 5, 6, 7, 8. Drain

#### PRODUCT SUMMARY

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)	
25	15 @ V <sub>GS</sub> = 10V	10	
	21 @ V <sub>GS</sub> = 4.5V	8	

#### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

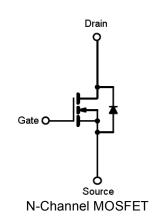
### **Application**

- Load Switch
- Dc-DC Converters and Motors Drivers

### **Ordering Information**

Part No.	Package	Packing
TSM4410CS RL	SOP-8	2.5Kpcs / 13" Reel

### **Block Diagram**



**Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	25	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Continuous Drain Current		I <sub>D</sub>	25	А	
Pulsed Drain Current	ed Drain Current		50	А	
Continuous Source Current (Diode C	onduction) <sup>a,b</sup>	I <sub>S</sub>	2.3	А	
Maximum Power Dissipation	Ta = 25°C	- P <sub>D</sub>	2	W	
	Ta = 70°C		1.3		
Operating Junction Temperature		T <sub>J</sub> +150		°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	$R\Theta_{JC}$	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	50	°C/W

#### Notes:

- a. Maximum DC current limited by the package
- b. Surface Mounted on 1" x 1" FR4 Board, t ≤ 10 sec.



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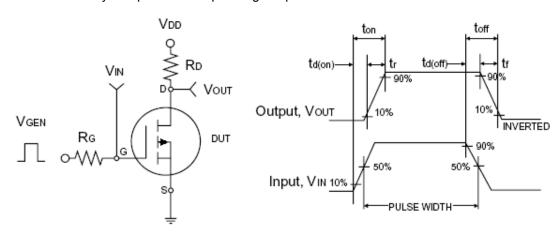


**Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV <sub>DSS</sub>	25			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	V <sub>GS(TH)</sub>	1.0	1.9	3.0	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 25V, V_{GS} = 0V$	I <sub>DSS</sub>			1.0	uA
On-State Drain Current	V <sub>DS</sub> ≥5V, V <sub>GS</sub> = 10V	I <sub>D(ON)</sub>	25			Α
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 10A$			13	15	0
Diaiii-Source Oii-State Resistance	n-Source On-State Resistance $V_{GS} = 4.5V, I_D = 8A$ $R_{DS(ON)}$		18	21	mΩ	
Forward Transconductance	$V_{DS} = 15V, I_{D} = 15A$	g <sub>fs</sub>		25		S
Diode Forward Voltage	$I_S = 2.3A$ , $V_{GS} = 0V$	V <sub>SD</sub>	1	0.85	1.3	V
Dynamic <sup>b</sup>						
Total Gate Charge	$V_{DS} = 15V, I_D = 10A,$	$Q_g$		14.7	26	
Gate-Source Charge		$Q_gs$		2.5		nC
Gate-Drain Charge	- V <sub>GS</sub> = 10V	$Q_{gd}$		3		1
Input Capacitance	., , , , , , , , , , , , , , , , , , ,	C <sub>iss</sub>		921		
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$	C <sub>oss</sub>		208.7		pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		108.2		
Switching <sup>c</sup>						
Turn-On Delay Time	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	t <sub>d(on)</sub>		20.2		
Turn-On Rise Time	$V_{DD} = 15V, R_L = 15\Omega,$	t <sub>r</sub>		5.9		0
Turn-Off Delay Time	$I_D = 1A, V_{GEN} = 10V,$ $R_G = 16\Omega$	t <sub>d(off)</sub>		49.5		nS
Turn-Off Fall Time	1012	t <sub>f</sub>		16.7		

#### Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

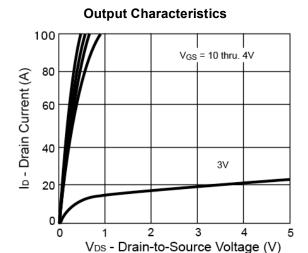
Switchin Waveforms



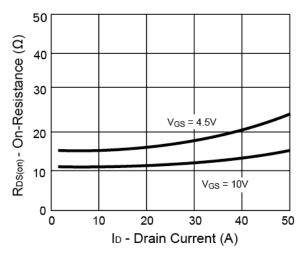
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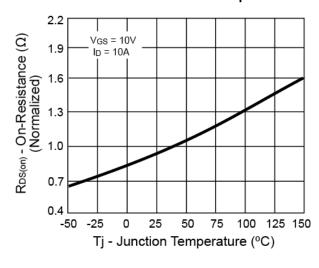
#### **Electrical Characteristics Curve** (Ta = 25°C, unless otherwise noted)



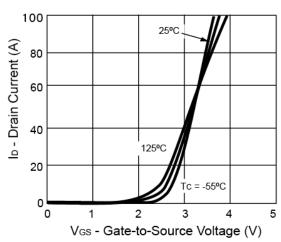
#### **On-Resistance vs. Drain Current**



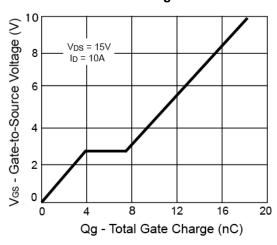
On-Resistance vs. Junction Temperature



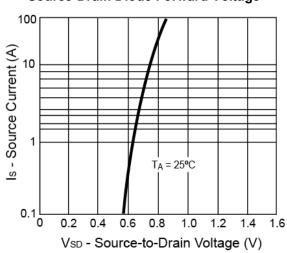
#### **Transfer Characteristics**



**Gate Charge** 



**Source-Drain Diode Forward Voltage** 





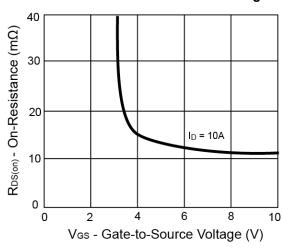




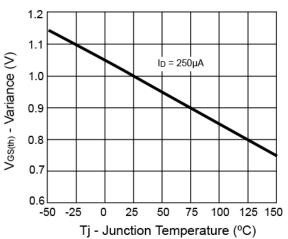


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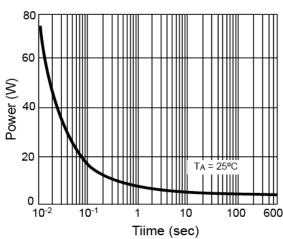
On-Resistance vs. Gate-Source Voltage



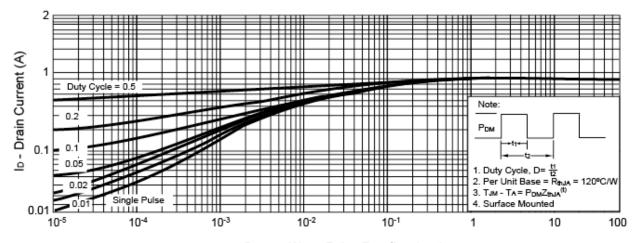
### Threshold Voltage



#### Single Pulse Power



#### Normalized Thermal Transient Impedance, Junction-to-Ambient

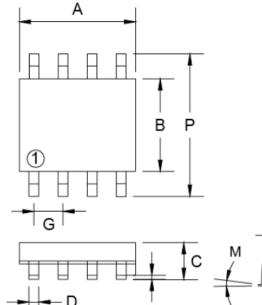


Square Wave Pulse Duration (sec)

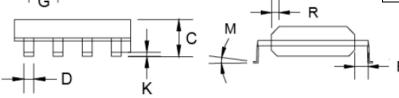
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# **SOP-8 Mechanical Drawing**



SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27BSC		0.05	BSC	
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	



## **Marking Diagram**



Y = Year Code

**M** = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code



## TSM4410 25V N-Channel MOSFET

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